

Title (en)
Sputtering target

Title (de)
Sputtertarget

Title (fr)
Cible de pulvérisation

Publication
EP 1895020 A1 20080305 (EN)

Application
EP 06729897 A 20060324

Priority
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Abstract (en)
Provided is a sputtering target having zinc sulfide and indium oxide, zinc oxide and oxide composed of another trivalent positive element A as its primary components, wherein the ratio of sulfur in relation to the total components is 5 to 30wt%, the (111) peak strength I1 of cubic crystal ZnS and the (100) peak strength I2 of hexagonal ZnS measured by XRD coexist, and I1 > I2 is satisfied. The present invention aims to provide a high-strength sputtering target capable of preventing cracks in a target upon manufacturing such a target or when forming a film via sputtering and a manufacturing method of such a sputtering target, as well as a thin film for an optical information recording medium optimal for use as a protective film and a manufacturing method of such a thin film.

IPC 8 full level
C23C 14/34 (2006.01); **C04B 35/453** (2006.01); **C04B 35/547** (2006.01); **C04B 35/626** (2006.01); **G11B 7/24** (2013.01); **G11B 7/254** (2013.01); **G11B 7/257** (2013.01); **G11B 7/2578** (2013.01); **G11B 7/2585** (2013.01); **G11B 7/26** (2006.01)

CPC (source: EP KR US)
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